



Future Normal in Semiconductor

2025년 2월 13일(목), 10:55-12:40

Room E(에메랄드 II+III), 5층

D. Thin Film Process Technology 분과

017_[TE2-D] Memory Capacitors

좌장: 안지훈 교수(한양대학교), 김건환 교수(연세대학교)

<p>TE2-D-1 10:55-11:10</p>	<p>Investigation of Atomic Layer Deposited SnO₂ Thin Films for Next-Generation DRAM Electrode Application InHong Hwang^{1,2} and In-Hwan Baek^{1,2} ¹Department of Chemistry and-Chemical Engineering, Inha University, ²Program in Semiconductor Convergence, Inha University</p>
<p>TE2-D-2 11:10-11:25</p>	<p>Achieving Equivalent Oxide Thickness Scaling of ZrO₂ Dielectric Thin Film via Gd Doping without Sacrificing Tetragonal Crystallinity Seungwoo Lee¹, Jihun Nam¹, Yoona Choi¹, Jonghwan Jeong¹, Min Kyeong Nam¹, Hansol Oh², Hanbyul Kim², Yongjoo Park², Youngjin Kim³, and Woojin jeon¹ ¹Department of Advanced Materials Engineering for Information and Electronics, and Integrated Education Program for Frontier Science & Technology (BK21 Four), Kyung Hee University, ²Advanced Research Development Team, SK Trichem Co. Ltd., ³Department of Chemical Engineering, Kyonggi University</p>
<p>TE2-D-3 11:25-11:40</p>	<p>Influence of Zr-Precursor Ligands on the Growth and Capacitor Properties of ZrO₂ Thin Films Grown by ALD Hyeongjun Kim¹, Haram Yang², and Woongkyu Lee^{1,2} ¹Department of Green Chemistry and Materials Engineering, Soongsil University, ²Department of Materials Science and Engineering, Soongsil University</p>
<p>TE2-D-4 11:40-11:55</p>	<p>Strategy for Stabilizing Metastable Rutile-Structured TiO₂ without Substrate Crystallographic Limitations Jihoon Jeon^{1,2} and Seong Keun Kim^{1,2} ¹Electronic Materials Research Center, KIST, ²KU-KIST Graduate School of Converging Science and Technology, Korea University</p>
<p>TE2-D-5 11:55-12:10</p>	<p>High Performance TiO₂-based DRAM Capacitors with Ultrathin ALD Sn-Doped MoO₂ Buffer Layer Jae Hyeon Lee and Jeong Hwan Han Department of Materials Science and Engineering, Seoul National University of Science and Technology</p>



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<p>TE2-D-6 12:10-12:25</p>	<p>Dielectrics with Sub-surface Dopant Implantation-Mediated Lattice Relaxation and V_0 Annihilation via Chemo-physical Plasma Annealing Gyuha Lee¹, Hyongjune Kim¹, Geongu Han², Sangwon Lee³, Jeongmin Oh³, and Jihwan An^{1,3} ¹Department of Mechanical Engineering, POSTECH, ²Department of Manufacturing Systems and Design Engineering, Seoul National University of Science and Technology, ³Graduate School of Semiconductor Technology, POSTECH</p>
<p>TE2-D-7 12:25-12:40</p>	<p>Synthesis of perovskite $SrTiO_3$ thin films by atomic layer deposition of SrF_2 and TiO_2 Jaejun Lee, Sangyeon Jeong, and Woongkyu Lee Department of Materials Science and Engineering, Soongsil University</p>